

ABSTRACT OF THE DISCLOSURE

A method for etching a tungsten-containing layer (**525**) on a substrate (**510**) substantially anisotropically, with good etching selectivity with respect to a hard mask layer, and without forming excessive passivating deposits on the etched features. In the method, the substrate (**510**) is placed in a plasma zone, and process gas mix comprising NF₃ and Cl₂ is introduced into the plasma zone. A plasma is formed from the process gas mix to anisotropically etch the tungsten containing layer (**525**) to produce patterned tungsten features (**535**).